

8550SS TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 1 \text{ W (Tamb=25°C)}$$

Collector current

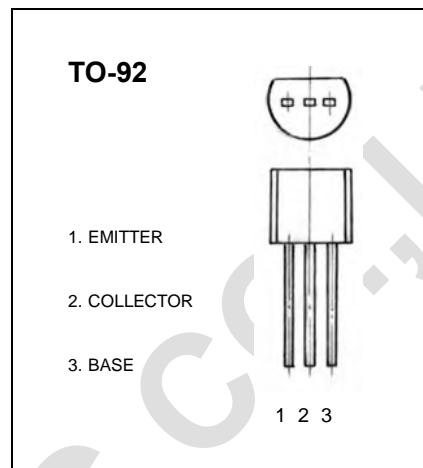
$$I_{CM}: -1.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	MA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100 \text{ mA}$	85		300	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -800 \text{ mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800 \text{ m}, I_B = -80 \text{ mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80 \text{ mA}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA$ $f = 30 \text{ MHz}$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range	85-160	120-200	160-300